	Application No.	Applicant(s)
	09/800,627	TANAKA ET AL
Notice of Allowability	Examiner	TANAKA ET AL. Art Unit
	Tonico M. Thomas	2022
	Toniae M. Thomas	2822
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this a or other appropriate communicati IGHTS. This application is subject	application. If not included ion will be mailed in due course. THIS
1. \boxtimes This communication is responsive to <u>the amendment filed</u>	on 27 Sep 2004.	
2. \boxtimes The allowed claim(s) is/are $\underline{1,4,8,12,16,20,24}$ and $\underline{53-64}$.		
3. \boxtimes The drawings filed on <u>03 July 2001</u> are accepted by the Ex	kaminer.	
 4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: Certified copies of the priority documents have Certified copies of the priority documents have Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 	e been received. e been received in Application No.	
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file a rep	ly complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give	itted. Note the attached EXAMINE es reason(s) why the oath or decla	ER'S AMENDMENT or NOTICE OF aration is deficient.
6. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.	
(a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached		
1) hereto or 2) to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date		
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t	.84(c)) should be written on the draw	wings in the front (not the back) of
7. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT	sit of BIOLOGICAL MATERIAL	_ must be submitted. Note the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0	6. ☐ Interview Summa Paper No./Mail D	Date
Paper No./Mail Date 09/27/04 4. Examiner's Comment Regarding Requirement for Deposit		
of Biological Material		ment of Reasons for Allowance

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EXAMINER'S AMENDMENT

Election/Restrictions

1. This application is in condition for allowance except for the presence of claims 2, 3, 5-7, 9-11, 13-15, 17-19, 21-23, and 25-52 non-elected without traverse. Accordingly, claims 2, 3, 5-7, 9-11, 13-15, 17-19, 21-23, and 25-52 have been cancelled.

Amendment

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

In claims

Claims 2, 3, 5-7, 9-11, 13-15, 17-19, 21-23, and 25-52 have been cancelled.

Reasons for Allowance

3. The following is an examiner's statement of reasons for allowance: the prior art record does not anticipate or render obvious a method for manufacturing a semiconductor device substantially as claimed. For example, Maekawa (US 6,066,547), which was relied upon in the final Office action mailed on 21 April 2004, discloses a method of manufacturing a semiconductor device. The method comprises the following steps substantially as claimed:

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forming a first semiconductor film comprising amorphous semiconductor over an insulating surface; introducing a metallic element for promoting crystallization into the first semiconductor film; partially crystallizing the first semiconductor film by a heat treatment to form a second semiconductor film in which crystal regions and amorphous regions are intermingled; and annealing the second semiconductor film. While Maekawa teaches that the second semiconductor film may be annealed using an excimer laser (col. 7, lines 47-49), Maekawa fails to anticipate, teach, or suggest laser annealing the second semiconductor film with a laser beam having a wavelength from 360 to 650 nm, so that the crystal regions generated by the heat treatment remain and mainly the amorphous regions are annealed. There is no teaching or suggestion within the prior art of record to modify Maekawa by using a laser having a wavelength from 360 to 650 nm to anneal the second semiconductor film substantially as claimed, so that the crystal regions generated by the heat treatment remain and mainly the amorphous regions are annealed.

4. The newly cited reference, Ohnuma et al. (US 2001,002544 A1) discloses a method of manufacturing a semiconductor device, wherein the method comprises: forming a first semiconductor film comprising amorphous semiconductor over an insulating surface; introducing a metallic element for promoting crystallization into the first semiconductor film; partially crystallizing the first semiconductor film by a heat treatment to form a second semiconductor film in which crystal regions and amorphous regions are

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intermingled; and laser annealing the second semiconductor film to crystallize the second semiconductor film (see, for example, the embodiment described in paragraphs 0081 to 0085). In a first embodiment, the laser annealing is performed using a XeCl excimer laser (par. 0081 to 0085); in a second embodiment, using a KrF excimer laser (paragraphs 0087 and 0088); in a third embodiment, using an ArF excimer laser (paragraphs 0091 and 0092); and in a fourth embodiment, using a third harmonic YAG laser (paragraphs 0095 to 0096). However, the Ohnuma patent differs from the claimed invention in that the patent fails to anticipate, teach, or suggest laser annealing the second semiconductor film with a laser beam having a wavelength from 360 to 650 nm. There is no teaching or suggestion within the prior art of record to modify Ohnuma by using a laser having a wavelength from 360 to 650 nm to anneal the second semiconductor film substantially as claimed.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Toniae M. Thomas whose telephone number is (571) 272-1846. The examiner can normally be reached on Monday-Thursday from 8:30 a.m. to 5:30 p.m..

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

JMJ

15 November 2004

Mary Wilczewski Primary Examiner